

# Kin M Yu

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

500  
papers

15,865  
citations

59  
h-index

110  
g-index

538  
ext. papers

17,113  
ext. citations

3.5  
avg, IF

6.03  
L-index

#	Paper	IF	Citations
500	On-wire axial perovskite heterostructures for monolithic dual-wavelength laser. <i>Nano Energy</i> , <b>2022</b> , 92, 106778	17.1	3
499	Effects of Al doping on the structural, electrical, and optical properties of rock-salt ZnCdO thin films grown by molecular beam epitaxy. <i>Journal of Physics and Chemistry of Solids</i> , <b>2022</b> , 163, 110571	3.9	1
498	Improved two-step photon absorption current by Cl-doping in ZnTeO-based intermediate band solar cells with n-ZnS layer. <i>Solar Energy Materials and Solar Cells</i> , <b>2022</b> , 235, 111456	6.4	1
497	Electronic structure and properties of Cu <sub>2-x</sub> S thin films: Dependence of phase structures and free-hole concentrations. <i>Applied Surface Science</i> , <b>2022</b> , 572, 151530	6.7	1
496	Amorphous CdO-In <sub>2</sub> O <sub>3</sub> alloy thin films with high conductivity and transparency synthesized by sol-gel method. <i>Journal of Alloys and Compounds</i> , <b>2022</b> , 893, 162341	5.7	0
495	Energy consumption modelling of a passive hybrid system for office buildings in different climates. <i>Energy</i> , <b>2022</b> , 239, 121914	7.9	3
494	Near-Infrared-Activated Thermochromic Perovskite Smart Windows.. <i>Advanced Science</i> , <b>2022</b> , e2106090	13.6	6
493	Effects of acceptor doping and oxygen stoichiometry on the properties of sputter-deposited p-type rocksalt Ni <sub>1-x</sub> Zn <sub>x</sub> O (0.3 ≤ x ≤ 1.0) alloys. <i>Journal of Alloys and Compounds</i> , <b>2022</b> , 905, 164224	5.7	1
492	Improving the p-type conductivity of Cu <sub>2</sub> O thin films by Ni doping and their heterojunction with n-ZnO. <i>Applied Surface Science</i> , <b>2022</b> , 590, 153047	6.7	1
491	Controlling electrical and optical properties of wurtzite Cd <sub>x</sub> Zn <sub>1-x</sub> O with high Cd contents via native defects manipulation by low-temperature annealing. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 175104	2.5	1
490	Doping limitation due to self-compensation by native defects in In-doped rocksalt CdZnO. <i>Journal of Physics Condensed Matter</i> , <b>2021</b> , 34,	1.8	1
489	Organic Hybrid Perovskite (MAPbI <sub>3</sub> Cl <sub>x</sub> ) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2010426	15.6	16
488	Self-Densified Optically Transparent VO Thermochromic Wood Film for Smart Windows. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 22495-22504	9.5	14
487	Highly transparent and conducting In doped CdO synthesized by sol-gel solution processing. <i>Journal of Materials Science</i> , <b>2021</b> , 56, 12607-12619	4.3	5
486	Structural, optical, and electrical properties of WZ- and RS-ZnCdO thin films on MgO (100) substrate by molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 867, 159033	5.7	2
485	Thermochromic Smart Windows: Organic Hybrid Perovskite (MAPbI <sub>3</sub> Cl <sub>x</sub> ) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width (Adv. Funct. Mater. 26/2021). <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2170186	15.6	3
484	Effect of Nitrogen Doping on Structural, Electrical, and Optical Properties of CuO Thin Films Synthesized by Radio Frequency Magnetron Sputtering for Photovoltaic Application. <i>ECS Journal of Solid State Science and Technology</i> , <b>2021</b> , 10, 065019	2	2

483	Two-Step Chemical Vapor Deposition-Synthesized Lead-Free All-Inorganic CsSbBr Perovskite Microplates for Optoelectronic Applications. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 35930-35940	9.5	4
482	Optoelectronic properties and doping of magnetron sputtered highly mismatched ZnO <sub>1-x</sub> Te <sub>x</sub> alloy thin films. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 852, 156950	5.7	2
481	Effective decoupling of seebeck coefficient and the electrical conductivity through isovalent substitution of erbium in bismuth selenide thermoelectric material. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 857, 157559	5.7	4
480	Mechanism of non-catalytic chemical vapor deposition growth of all-inorganic CsPbX <sub>3</sub> (X = Br, Cl) nanowires. <i>Journal of Materials Chemistry C</i> , <b>2021</b> , 9, 3229-3238	7.1	2
479	Flexibility of Room-Temperature-Synthesized Amorphous CdO-InO Alloy Films and Their Application as Transparent Conductors in Solar Cells. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 43795-43805	9.5	1
478	Electrical conductivity and effects of mechanical bending of flexible amorphous transparent conducting CdO-Ga <sub>2</sub> O <sub>3</sub> films synthesized by room temperature sputtering. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 875, 160000	5.7	1
477	Effects of free carriers on the optical properties of high mobility transition metal doped In <sub>2</sub> O <sub>3</sub> transparent conductors. <i>Physical Review Materials</i> , <b>2021</b> , 5,	3.2	1
476	Band alignment of wide bandgap NiO/MoO <sub>3</sub> and NiO/WO <sub>3</sub> p-n heterojunctions studied by high-resolution X-ray photoelectron spectroscopy. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 876, 160136	5.7	4
475	Potential building energy savings by passive strategies combining daytime radiative coolers and thermochromic smart windows. <i>Case Studies in Thermal Engineering</i> , <b>2021</b> , 28, 101517	5.6	3
474	Reversible photochromic and photoluminescence in iodide perovskites. <i>Thin Solid Films</i> , <b>2021</b> , 737, 138950	5.0	1
473	Synthesis of New Nitride Alloys with Mg by Plasma-Assisted Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 2000122	1.3	1
472	Realization of rocksalt Zn <sub>1-x</sub> Cd <sub>x</sub> O thin films with an optical band gap above 3.0 eV by molecular beam epitaxy. <i>CrystEngComm</i> , <b>2020</b> , 22, 2781-2787	3.3	5
471	Effect of oxygen flow rate on properties of Cu <sub>4</sub> O <sub>3</sub> thin films fabricated by radio frequency magnetron sputtering. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 085302	2.5	7
470	Wide-Gap Zn <sub>1-x</sub> Ni <sub>x</sub> O Alloy: A Transparent p-Type Oxide. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	10
469	Room temperature sputtered Cu doped NiO <sub>1-x</sub> p-type conductivity, stability of electrical properties and p-n heterojunction. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 835, 155269	5.7	9
468	Rapid thermal annealing assisted facile solution method for tungsten-doped vanadium dioxide thin films on glass substrate. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 833, 155053	5.7	12
467	Efficient p-type doping of sputter-deposited NiO thin films with Li, Ag, and Cu acceptors. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	9
466	Conduction band modifications by d states in vanadium doped CdO. <i>Journal of Alloys and Compounds</i> , <b>2020</b> , 822, 153567	5.7	4

465	Bio-inspired TiO nano-cone antireflection layer for the optical performance improvement of VO thermochromic smart windows. <i>Scientific Reports</i> , <b>2020</b> , 10, 11376	4.9	7
464	Controllable optical emission wavelength in all-inorganic halide perovskite alloy microplates grown by two-step chemical vapor deposition. <i>Nano Research</i> , <b>2020</b> , 13, 2939-2949	10	12
463	Morphology and strain control of hierarchical cobalt oxide nanowire electrocatalysts via solvent effect. <i>Nano Research</i> , <b>2020</b> , 13, 3130-3136	10	7
462	Vacancy defects induced changes in the electronic and optical properties of NiO studied by spectroscopic ellipsometry and first-principles calculations. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 135705 <sup>2-5</sup>	2.5	22
461	Temperature-dependent growth of hexagonal and monoclinic gallium sulfide films by pulsed-laser deposition. <i>AIP Advances</i> , <b>2020</b> , 10, 105215	1.5	2
460	Controlling the p-Type Conductivity and Composition Range for Bipolar Conduction in NixCd1-xO Alloys by Acceptor Doping. <i>Journal of Physical Chemistry C</i> , <b>2020</b> , 124, 20000-20009	3.8	4
459	Nitrogen Doping Effect in Cu4O3 Thin Films Fabricated by Radio Frequency Magnetron Sputtering. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900363	1.3	4
458	Stoichiometry Controlled Bipolar Conductivity in Nanocrystalline NixCd1-xO1+x Thin Films. <i>Physical Review Applied</i> , <b>2019</b> , 11,	4.3	13
457	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 083106	2.5	2
456	Amorphous gallium oxide sulfide: A highly mismatched alloy. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 105708 <sup>5</sup>	2.5	3
455	Three-dimensional band structure and surface electron accumulation of rs-CdZnO studied by angle-resolved photoemission spectroscopy. <i>Scientific Reports</i> , <b>2019</b> , 9, 8026	4.9	5
454	ZnO1-xTex highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 155702	2.5	7
453	Electronically Controlled Chemical Stability of Compound Semiconductor Surfaces. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 32543-32551	9.5	
452	Cl-doping effect in ZnTe1-xOx highly mismatched alloys for intermediate band solar cells. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 243109	2.5	4
451	Effects of oxygen stoichiometry on the phase stability of sputter-deposited CdxZn1-xO alloys. <i>Physical Review Materials</i> , <b>2019</b> , 3,	3.2	7
450	Mg induced compositional change in InGaN alloys. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 025018 <sup>1.8</sup>	1.8	3
449	Effects of doping and rapid thermal processing in Y doped CdO thin films. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 776, 259-265	5.7	7
448	Room-Temperature-Synthesized High-Mobility Transparent Amorphous CdO-GaO Alloys with Widely Tunable Electronic Bands. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 7239-7247	9.5	11

447	Room-Temperature Red-Green-Blue Whispering-Gallery Mode Lasing and White-Light Emission from Cesium Lead Halide Perovskite (CsPbX <sub>3</sub> , X = Cl, Br, I) Microstructures. <i>Advanced Optical Materials</i> , <b>2018</b> , 6, 1700993	8.1	33
446	Growth behavior of co-electrodeposited CZTS precursor thin films from acidic baths containing tartaric acid. <i>Materials Chemistry and Physics</i> , <b>2018</b> , 204, 83-94	4.4	17
445	Improved photovoltaic properties of ZnTeO-based intermediate band solar cells <b>2018</b> ,		2
444	Oxygen vibrational modes in ZnS <sub>1-x</sub> O <sub>x</sub> alloys. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161537	2.5	2
443	Engineering Electronic Band Structure of Indium-doped Cd <sub>1-x</sub> Mg <sub>x</sub> O Alloys for Solar Power Conversion Applications. <i>Energy Technology</i> , <b>2018</b> , 6, 122-126	3.5	4
442	THz transient photoconductivity of the III-V dilute nitride GaP <sub>1-y</sub> As <sub>y</sub> N <sub>x</sub> . <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 125009	1.8	1
441	Growth and characterization of Zn <sub>1-x</sub> Cd <sub>x</sub> Te <sub>1-y</sub> O <sub>y</sub> highly mismatched alloys for intermediate band solar cells. <i>Solar Energy Materials and Solar Cells</i> , <b>2017</b> , 169, 1-7	6.4	6
440	. <i>IEEE Journal of Photovoltaics</i> , <b>2017</b> , 7, 1024-1030	3.7	9
439	Multicolor emission from intermediate band semiconductor ZnOSe. <i>Scientific Reports</i> , <b>2017</b> , 7, 44214	4.9	11
438	High mobility transparent amorphous CdO-In <sub>2</sub> O <sub>3</sub> alloy films synthesized at room temperature. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 072108	3.4	8
437	Effects of Ni d-levels on the electronic band structure of Ni <sub>x</sub> Cd <sub>1-x</sub> O semiconducting alloys. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 185703	2.5	9
436	Surface modification of NiCdO barrier layer in complex photoanodes and TiO <sub>2</sub> protective coating for efficient and stable water dissociation. <i>Journal of Solid State Electrochemistry</i> , <b>2017</b> , 21, 803-812	2.6	
435	On the Use of Transparent Conductive Oxides in High Concentrator III-V Multijunction Solar Cells <b>2017</b> ,		1
434	Intermixing studies in GaN <sub>1-x</sub> Sb <sub>x</sub> highly mismatched alloys. <i>Applied Optics</i> , <b>2017</b> , 56, B64-B69	0.2	3
433	On-Nanowire Axial Heterojunction Design for High-Performance Photodetectors. <i>ACS Nano</i> , <b>2016</b> , 10, 8474-81	16.7	73
432	Mechanistic insights into chemical and photochemical transformations of bismuth vanadate photoanodes. <i>Nature Communications</i> , <b>2016</b> , 7, 12012	17.4	169
431	Highly mismatched GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: synthesis, structure and electronic properties. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 083001	1.8	13
430	Multicolor Electroluminescence from Intermediate Band Solar Cell Structures. <i>Advanced Energy Materials</i> , <b>2016</b> , 6, 1501820	21.8	10

429	Compositional dependence of optical transition energies in highly mismatched Zn <sub>1-x</sub> Cd <sub>x</sub> Te <sub>1-y</sub> O <sub>y</sub> alloys. <i>Applied Physics Express</i> , <b>2016</b> , 9, 021202	2.4	5
428	Electrochemical modification of the optical and electrical properties of Cd-rich Ni <sub>1-x</sub> Cd <sub>x</sub> O alloys. <i>Solar Energy Materials and Solar Cells</i> , <b>2016</b> , 147, 127-133	6.4	6
427	Controlling disorder-mediated exchange bias in (Mn,Zn,Fe) <sub>3</sub> O <sub>4</sub> thin films. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2016</b> , 405, 129-136	2.8	4
426	Undoped p-type GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: Effects of annealing. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 252102	3.4	5
425	Band structure of germanium carbides for direct bandgap silicon photonics. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 053102	2.5	15
424	Defects and properties of cadmium oxide based transparent conductors. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 181501	2.5	26
423	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. <i>Physical Review Applied</i> , <b>2016</b> , 6,	4.3	41
422	Semiempirical modeling of a three sublayer photoanode for highly efficient photoelectrochemical water splitting: Parameter and electrolyte optimizations. <i>Solar Energy Materials and Solar Cells</i> , <b>2016</b> , 157, 190-199	6.4	3
421	Improvement in the electronic quality of pulsed laser deposited CuIn <sub>0.7</sub> Ga <sub>0.3</sub> Se <sub>2</sub> thin films via post-deposition elemental sulfur annealing process. <i>Thin Solid Films</i> , <b>2016</b> , 608, 50-56	2.2	9
420	Formation of Nanoscale Composites of Compound Semiconductors Driven by Charge Transfer. <i>Nano Letters</i> , <b>2016</b> , 16, 5247-54	11.5	9
419	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 085018	1.8	14
418	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 393-397	1.6	7
417	. <i>IEEE Journal of Photovoltaics</i> , <b>2015</b> , 5, 878-884	3.7	5
416	Effects of native defects on properties of low temperature grown, non-stoichiometric gallium nitride. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 385101	3	5
415	Exploration of the growth parameter space for MBE-grown GaN <sub>1-x</sub> B <sub>x</sub> highly mismatched alloys. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 255-257	1.6	8
414	Temperature evolution of carrier dynamics in GaN <sub>x</sub> PyAs <sub>1-x</sub> alloys. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 175702	2.5	15
413	Effects of the d-donor level of vanadium on the properties of Zn <sub>1-x</sub> V <sub>x</sub> O films. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 182101	3.4	9
412	Indium doped Cd <sub>1-x</sub> Zn <sub>x</sub> O alloys as wide window transparent conductors. <i>Thin Solid Films</i> , <b>2015</b> , 597, 183-187	2.2	6

411	Highly uniform and stable n-type carbon nanotube transistors by using positively charged silicon nitride thin films. <i>Nano Letters</i> , <b>2015</b> , 15, 392-7	11.5	82
410	Growth and characterization of highly mismatched Zn <sub>1-x</sub> CdxTe <sub>1-y</sub> Oy alloys for intermediate band solar cells <b>2015</b> ,		1
409	Evidence of extreme type-III band offset at buried n-type CdO/p-type SnTe interfaces. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	7
408	Growth and characterization of ZnO <sub>1-x</sub> Sx highly mismatched alloys over the entire composition. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 215702	2.5	36
407	Electronic band structure of highly mismatched GaN <sub>1-x</sub> Sbx alloys in a broad composition range. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 142104	3.4	23
406	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. <i>Journal of Physics: Conference Series</i> , <b>2015</b> , 647, 012067	0.3	
405	Self-Passivation of Defects: Effects of High-Energy Particle Irradiation on the Elastic Modulus of Multilayer Graphene. <i>Advanced Materials</i> , <b>2015</b> , 27, 6841-7	24	21
404	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi <sub>2</sub> Te <sub>3</sub> by Multifunctionality of Native Defects. <i>Advanced Materials</i> , <b>2015</b> , 27, 3681-6	24	79
403	Electronic band structure of ZnO-rich highly mismatched ZnO <sub>1-x</sub> Tex alloys. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 092101	3.4	24
402	Determination of N-/Ga-rich growth conditions, using in-situ auger electron spectroscopy. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 2-4	1.6	3
401	Bi flux-dependent MBE growth of GaSbBi alloys. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 241-244	1.6	24
400	NixCd <sub>1-x</sub> O: Semiconducting alloys with extreme type III band offsets. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 022110	3.4	16
399	Fermi-level stabilization in the topological insulators Bi <sub>2</sub> Se <sub>3</sub> and Bi <sub>2</sub> Te <sub>3</sub> : Origin of the surface electron gas. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	39
398	Modeling of the atomic structure and electronic properties of amorphous GaN <sub>1-x</sub> Asx. <i>Computational Materials Science</i> , <b>2014</b> , 82, 100-106	3.2	12
397	Growth and characterization of highly mismatched GaN <sub>1-x</sub> Sbx alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 123704	2.5	18
396	InGaN doping for high carrier concentration in plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 381-384		11
395	Surface hole accumulation and Fermi level stabilization energy in SnTe. <i>Applied Physics Express</i> , <b>2014</b> , 7, 091201	2.4	7
394	Theoretical and experimental studies of electronic band structure for GaSb <sub>1-x</sub> Bix in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 355107	3	46



393	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 043511	2.5	60
392	Tellurium n-type doping of highly mismatched amorphous GaN <sub>1-x</sub> As alloys in plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2014</b> , 404, 9-13	1.6	3
391	Substitutionality of nitrogen atoms and formation of nitrogen complexes and point defects in GaPN alloys. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 075106	3	9
390	. <i>IEEE Journal of Photovoltaics</i> , <b>2014</b> , 4, 196-201	3.7	18
389	Bi-induced band gap reduction in epitaxial InSbBi alloys. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 212101	3.4	38
388	Improved ion implant fluence uniformity in hydrogen enhanced glow discharge plasma immersion ion implantation into silicon. <i>Review of Scientific Instruments</i> , <b>2014</b> , 85, 063506	1.7	2
387	Facile Synthesis of [Cu(SCH <sub>3</sub> )] Nanowires with High Charge Mobility. <i>ChemPlusChem</i> , <b>2014</b> , 79, 559-563	2.8	7
386	Composition determination of quaternary GaAsPN layers from single X-ray diffraction measurement of quasi-forbidden (002) reflection. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 203102	2.5	8
385	Fermi level stabilization and band edge energies in Cd <sub>x</sub> Zn <sub>1-x</sub> O alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 233708	2.5	31
384	Surface photovoltage and modulation spectroscopy of E <sub>1</sub> and E <sub>1</sub> <sup>+</sup> transitions in GaNAs layers. <i>Thin Solid Films</i> , <b>2014</b> , 567, 101-104	2.2	14
383	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 132103	3.4	22
382	Composition and optical properties of dilute-Sb GaN <sub>1-x</sub> Sbx highly mismatched alloys grown by MBE. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 465102	3	9
381	. <i>IEEE Journal of Photovoltaics</i> , <b>2013</b> , 3, 730-736	3.7	19
380	Growth and properties of GaSbBi alloys. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 142106	3.4	78
379	Single crystalline In <sub>x</sub> Ga <sub>1-x</sub> N layers on germanium by molecular beam epitaxy. <i>CrystEngComm</i> , <b>2013</b> , 15, 9121	3.3	6
378	Temperature dependence of the band gap of GaSb <sub>1-x</sub> Bi <sub>x</sub> alloys with 0 < x < 1. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 261907	3.4	40
377	Molecular beam epitaxial growth of ZnCdTeO epilayers for intermediate band solar cells. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 259-262	1.6	11
376	Microstructure of GaN <sub>1-x</sub> Bi <sub>x</sub> . <i>Journal of Electronic Materials</i> , <b>2013</b> , 42, 26-32	1.9	4



375	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 112105	3.4	32
374	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 052111	3.4	50
373	Crystal structure and properties of CdxZn1-xO alloys across the full composition range. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 232103	3.4	52
372	GaN1-xSbx highly mismatched alloys grown by low temperature molecular beam epitaxy under Ga-rich conditions. <i>Journal of Crystal Growth</i> , <b>2013</b> , 383, 95-99	1.6	13
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212	Compositional modulation in In(x)Ga(1-x)N: TEM and X-ray studies. <i>Microscopy (Oxford, England)</i> , <b>2005</b> , 54, 243-50	1.3	17
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